

REMARKS

Applicant will address each of the Examiner's objections and rejections in the order in which they appear in the Final Rejection.

Claim Rejections - 35 USC §112

The Examiner rejects Claims 1-24 under 35 USC §112, second paragraph, as being indefinite. In particular, the Examiner objects to the phrase a "crystalline semiconductor film" in the claims.

In order to advance the prosecution of this application, Applicant has amended Claims 1, 13 and 19 to remove the objected to language. Accordingly, it is requested that this rejection now be withdrawn

Claim Rejections - 35 USC §102

The Examiner also rejects Claim s1-24 under 35 U.S.C. 102(b) as being anticipated by Japanese laid open applications 08-254713 (herein "Fukuda"). This rejection is respectfully traversed.

In the Final Rejection, the Examiner appears to be relying on the previous office action for his explanation that the cited reference includes all of the structural features of the claimed invention. Previously, the Examiner stated that "for example, comparing applicant's claim 1 structure with Fig. 1 of Fukuda, there is seen a semiconductor device having a gate (2) formed on an insulating surface (1), a gate insulating film (3a and 3b) formed on the gate electrode, source, drain, and channel region formed on the gate insulator layer, and where the gate insulating film includes a layer of silicon nitride oxide (3a) containing boron" (emphasis added).

Independent Claim 1 of the present application, however, recites that the source region and the drain region are in contact with the gate insulating film, wherein the insulating film includes a layer of silicon nitride oxide containing boron. Independent Claims 13 and 19 have been amended in a similar manner.

In contrast, Fig. 1 of Fukuda clear shows that the source region and the drain region are NOT in contact with the (gate) insulating film. Hence, Fukuda fails to disclose or suggest the device of independent Claims 1, 13 and 19, or those claims dependent thereon.

With regard to independent Claim 7, this claim recites that the gate insulating film includes a layer of a silicon nitride oxide film containing boron and that the gate insulating film is on the channel formation region. In contrast, Fukuda shows the channel formation region on the gate insulating film. Hence, the claimed invention is different and is not disclosed or suggested by the cited reference.

Therefore, for at least the above-stated reasons, the cited reference fails to disclose or suggest the claimed invention. Accordingly, it is respectfully requested that this rejection be withdrawn.

New Claims

Applicant is adding new dependent Claims 32-35 herewith. Please charge our deposit account 50/1039 for any fee due for such claims.

IDS

Applicant is included an IDS herewith. It is requested that this IDS be considered before any further action is entered in this application.

Conclusion

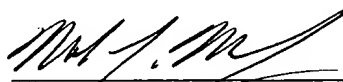
Applicant respectfully submits that the present application is now in a condition for allowance and should be allowed.

Please charge our deposit account 50/1039 for any fee due for this amendment.

Favorable reconsideration is earnestly solicited.

Respectfully submitted,

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